

L Number	Hits	Search Text	DB	Time stamp
12	86594	(dynamic near random near access near memory) dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 12:32
13	10229	shallow near3 isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 12:33
14	509780	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 12:33
15	4266	collar near3 (dielectric insulat\$3 layer film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 12:33
16	249	((dynamic near random near access near memory) dram) and (shallow near3 isolation) and capacitor and (collar near3 (dielectric insulat\$3 layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 12:34